

In re Patent Application of:
GRANT
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In the Specification:

Please replace paragraph [0022] on page 5 with the following rewritten paragraph:

With reference to FIG. 1, a pixel indicated generally at 101 is formed on a p-type substrate 118 with a photosensing part 102 and an active part 104. The photosensing part 102 comprises a partially pinned photo-diode formed from an n-type well 116 within the substrate 118 and a p-type pinning layer 106 partially covering the n-type well 116. The active part 104 comprises an NMOS transistor 112 formed from two spaced apart, highly doped n-type implants 110 in a p-type well 114. The n-type well 116 is positioned to connect the photo sensing and active parts 102, 104 respectively. The p-type pinning layer 106 has an anti-reflection coating 130 of silicon nitride on silicon dioxide.